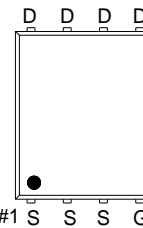
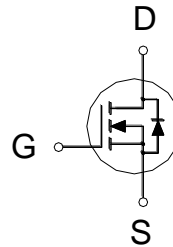




PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	5.25m Ω	64A



G. GATE
D. DRAIN
S. SOURCE

100% UIS Tested
100% Rg Tested

Features

- Pb-Free, Halogen Free and RoHS compliant.
- Low $R_{DS(on)}$ to Minimize Conduction Losses.
- Ohmic Region Good $R_{DS(on)}$ Ratio.
- Optimized Gate Charge to Minimize Switching Losses.

Applications

- Protection Circuits Applications.
- Logic/Load Switch Circuits Applications.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 25	V
Continuous Drain Current ⁴	$T_C = 25\text{ }^\circ\text{C}$	I_D	64	A
	$T_C = 100\text{ }^\circ\text{C}$		40	
Pulsed Drain Current ¹		I_{DM}	120	
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	I_D	20	
	$T_A = 70\text{ }^\circ\text{C}$		16	
Avalanche Current		I_{AS}	33	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	54	mJ
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	41	W
	$T_C = 100\text{ }^\circ\text{C}$		16.5	
Power Dissipation ³	$T_A = 25\text{ }^\circ\text{C}$	P_D	4.1	W
	$T_A = 70\text{ }^\circ\text{C}$		2.7	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$t \leq 10s$	$R_{\theta JA}$		30	°C / W
Junction-to-Ambient ²	Steady-State	$R_{\theta JA}$		51	
Junction-to-Case	Steady-State	$R_{\theta JC}$		3	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$.

³The Power dissipation is based on $R_{\theta JA} t \leq 10s$ value.

⁴Package limitation current is 35A.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ C$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3	1.5	2.3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 25V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$			1	μA
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 55^\circ C$			10	
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 8.8A$		5.4	7.5	m Ω
		$V_{GS} = 10V, I_D = 11A$		3.5	5.25	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 11A$		36		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		1009		pF
Output Capacitance	C_{oss}			327		
Reverse Transfer Capacitance	C_{rss}			195		
Gate Resistance	R_g	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		1.6		Ω
Total Gate Charge ²	Q_g	$V_{GS} = 10V$		23		nC
		$V_{GS} = 4.5V$		13		
Gate-Source Charge ²	Q_{gs}	$V_{DS} = 15V, V_{GS} = 10V, I_D = 11A$		2		
Gate-Drain Charge ²	Q_{gd}			7.6		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = 15V, I_D \cong 11A, V_{GS} = 10V, R_{GEN} = 6\Omega$		23		nS
Rise Time ²	t_r			25		
Turn-Off Delay Time ²	$t_{d(off)}$			50		
Fall Time ²	t_f			21		

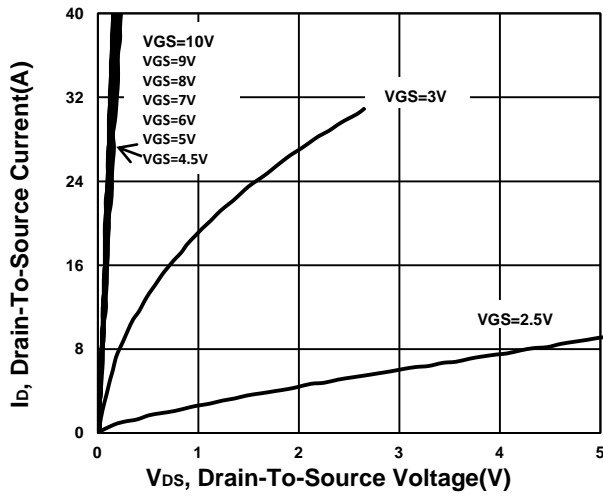
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)

Continuous Current	I _S			25	A
Forward Voltage ¹	V _{SD}	I _F = 11A, V _{GS} = 0V		1.2	V
Reverse Recovery Time	t _{rr}	I _F = 11A, di _F /dt = 100A / μS		21	nS
Reverse Recovery Charge	Q _{rr}			7.8	nC

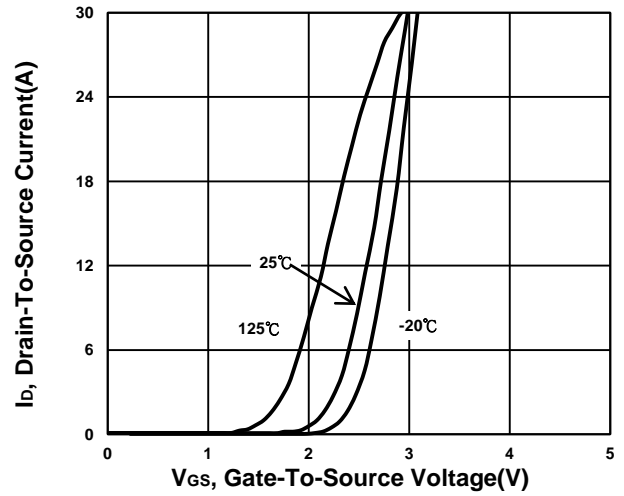
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

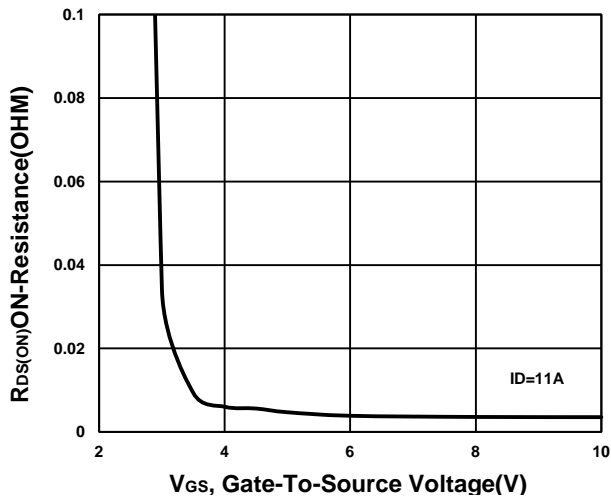
Output Characteristics



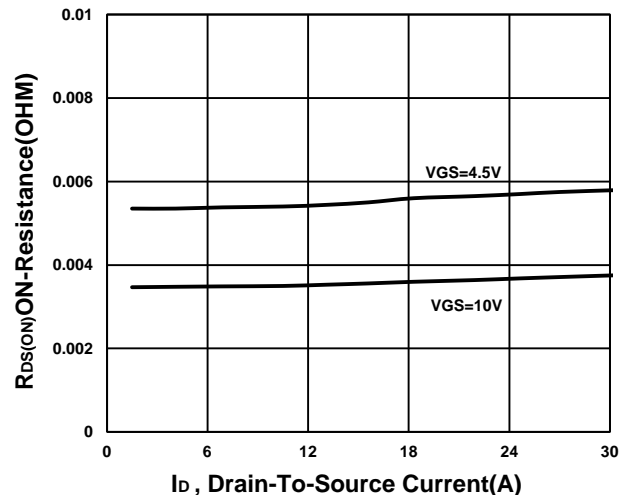
Transfer Characteristics



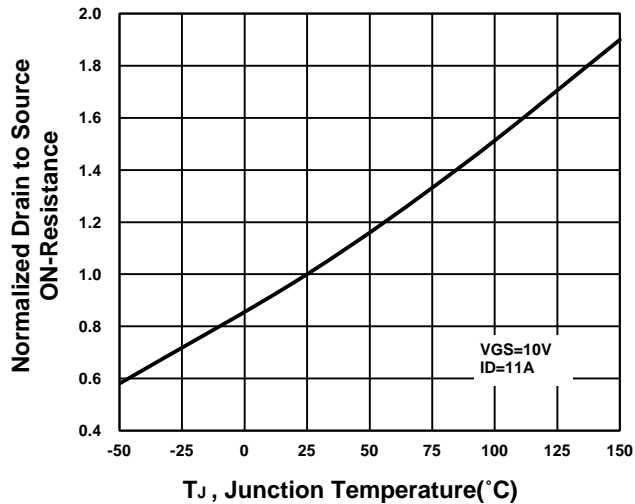
On-Resistance VS Gate-To-Source



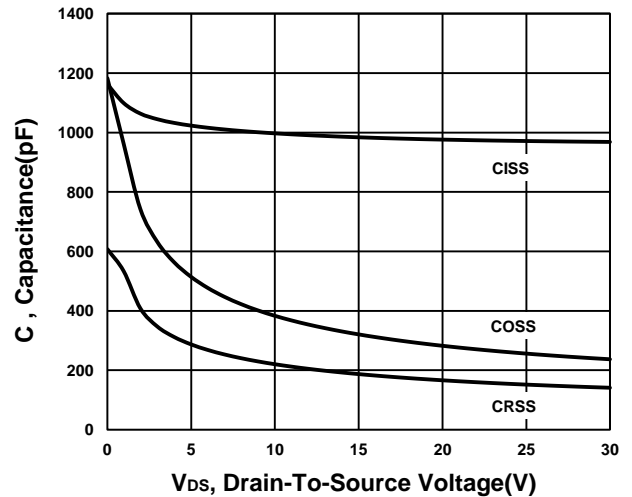
On-Resistance VS Drain Current



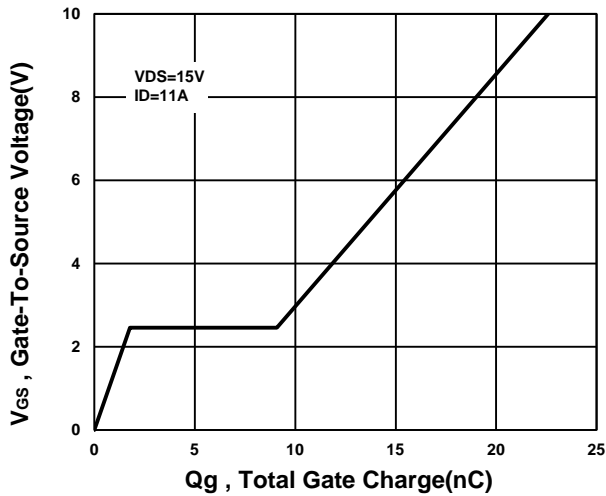
On-Resistance VS Temperature



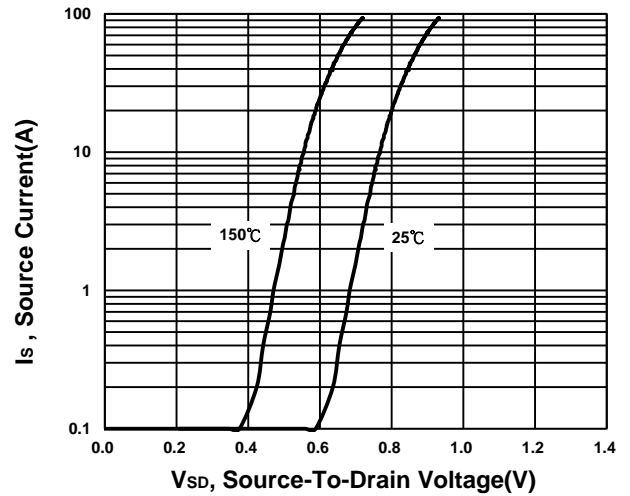
Capacitance Characteristic



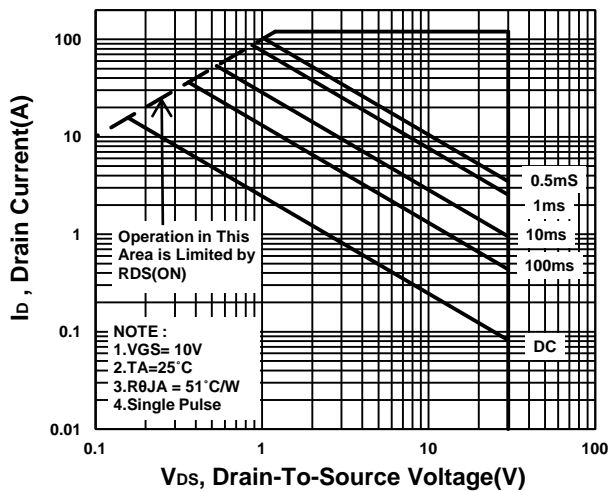
Gate charge Characteristics



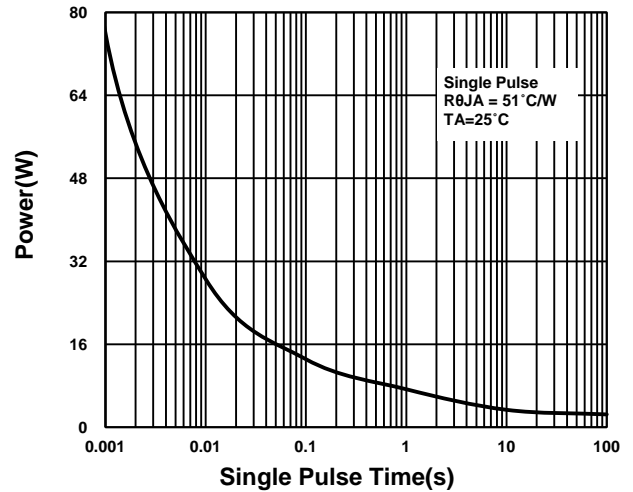
Source-Drain Diode Forward Voltage



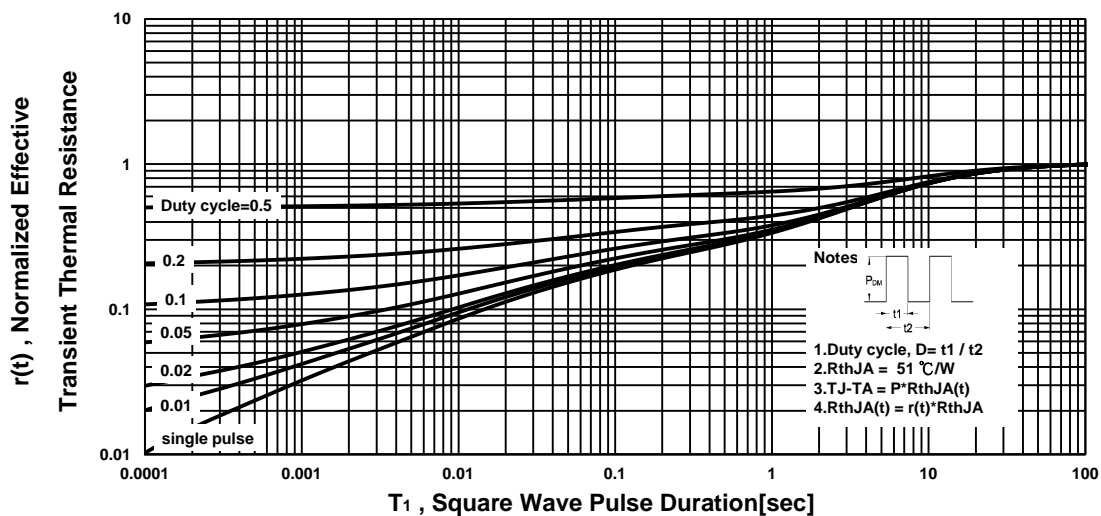
Safe Operating Area



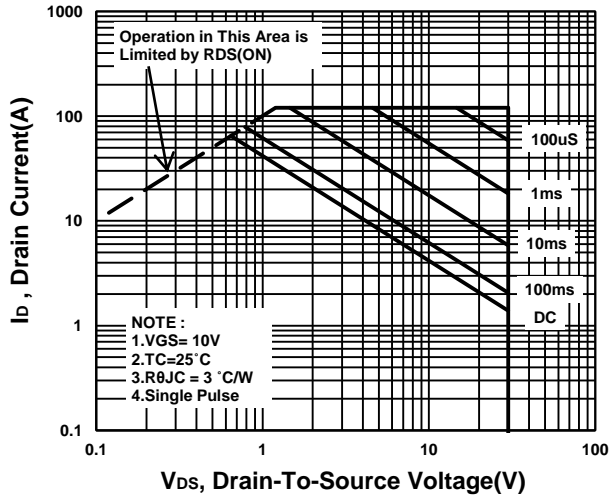
Single Pulse Maximum Power Dissipation



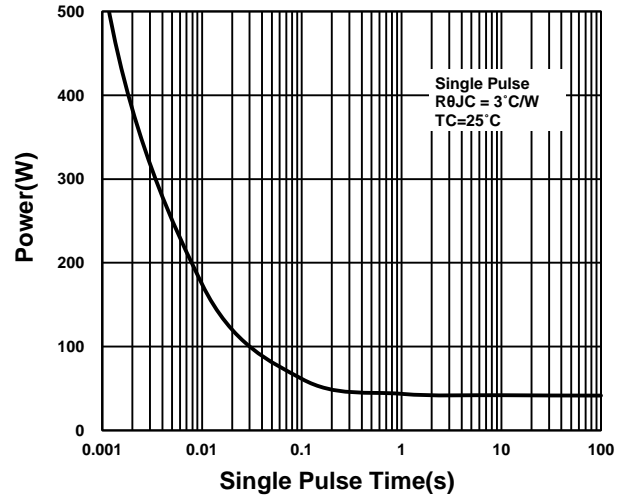
Transient Thermal Response Curve



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

